
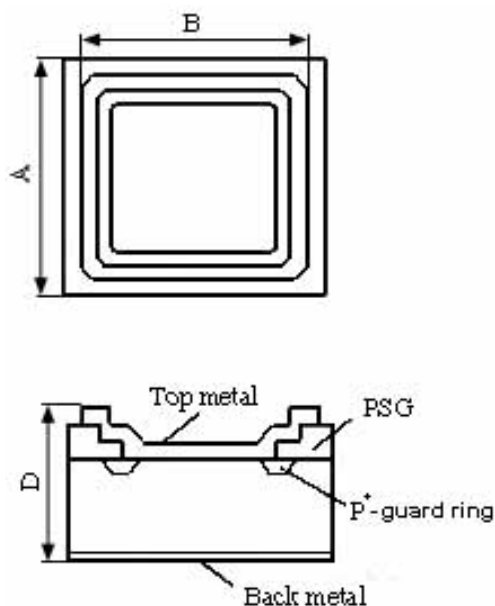


SCHOTTKY DIODES KDN-10040.



Rev.1. Feb. 2010

 VSP-MIKRON		10A/40V. Die Size-90mil.		
Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	V_{BR}	V	40	45
Average Rectified Forward Current	$I_{F(AV)}$	A	10,0	-
DC Forward Voltage @ 25°C , $I_F=10,0\text{A}$	V_F	V	0,57	0,55
Maximum Reverse Current @ 25°C , $V_R=45\text{V}$ 25°C , $V_R=40\text{V}$ 125°C , $V_R=40\text{V}$	I_R	mA	- 0,200 110,0	0,200 0,150 100,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	150	-
Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$, $f=1\text{kHz}$., $T_J<150^\circ\text{C}$.	I_{RRM}	A	3,5	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	± 8 (contact)	
Voltage Rate of Change	dV/dt	$\text{V}/\mu\text{S}$	10.000	
Operating Junction Temperature	T_J	$^\circ\text{C}$	150	



DIM	ITEM	μm
A_x A_y	Wafer Form Die Size	2280
B_x B_y	Top Metal Size	2140
D	Thickness	350max.
Scribe line Width		80

Top metal: a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.